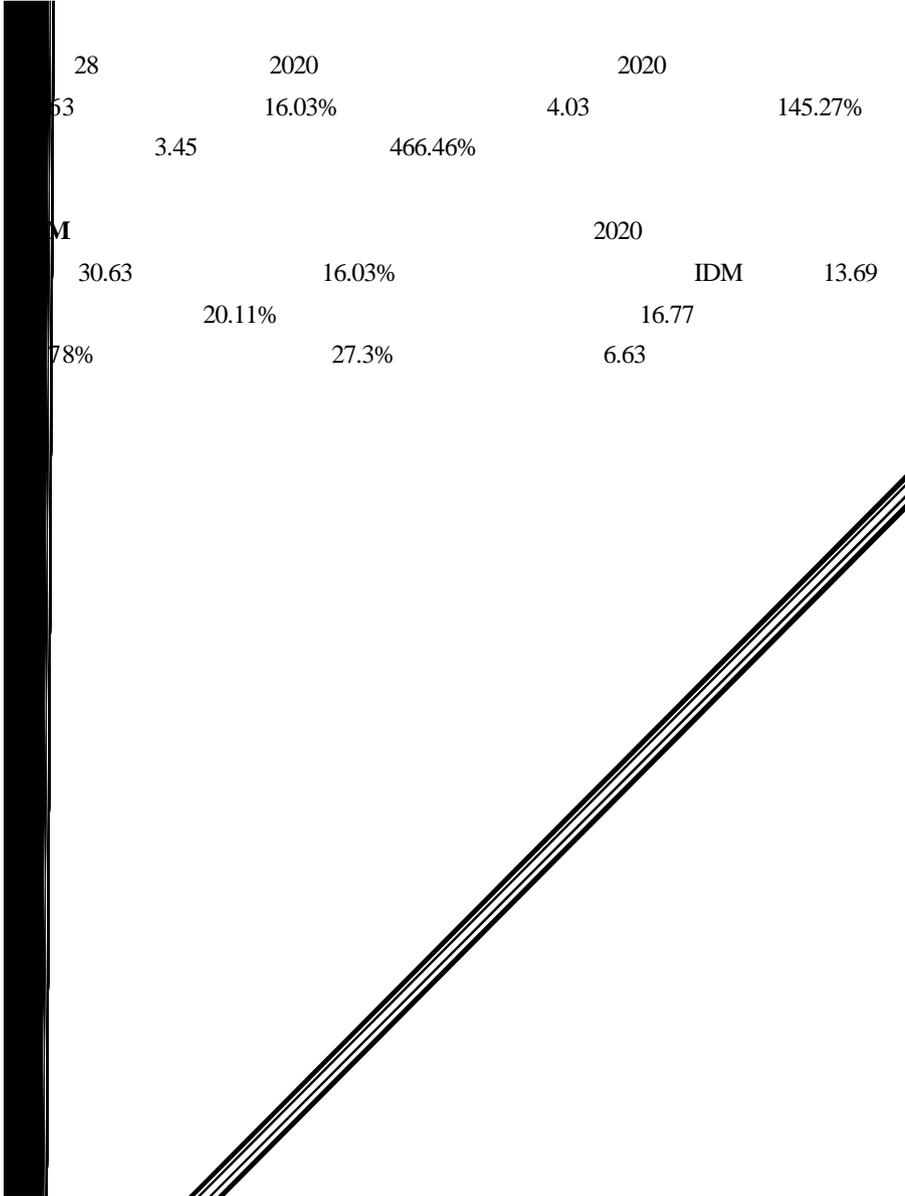


/

IDM



IDM			
IGBT	49.90%	MOSFET	21.43%
50%	IDM		
	11.5%		
	27.3%	6.63	
		2019	
IDM	44.71%	43.18%	

1

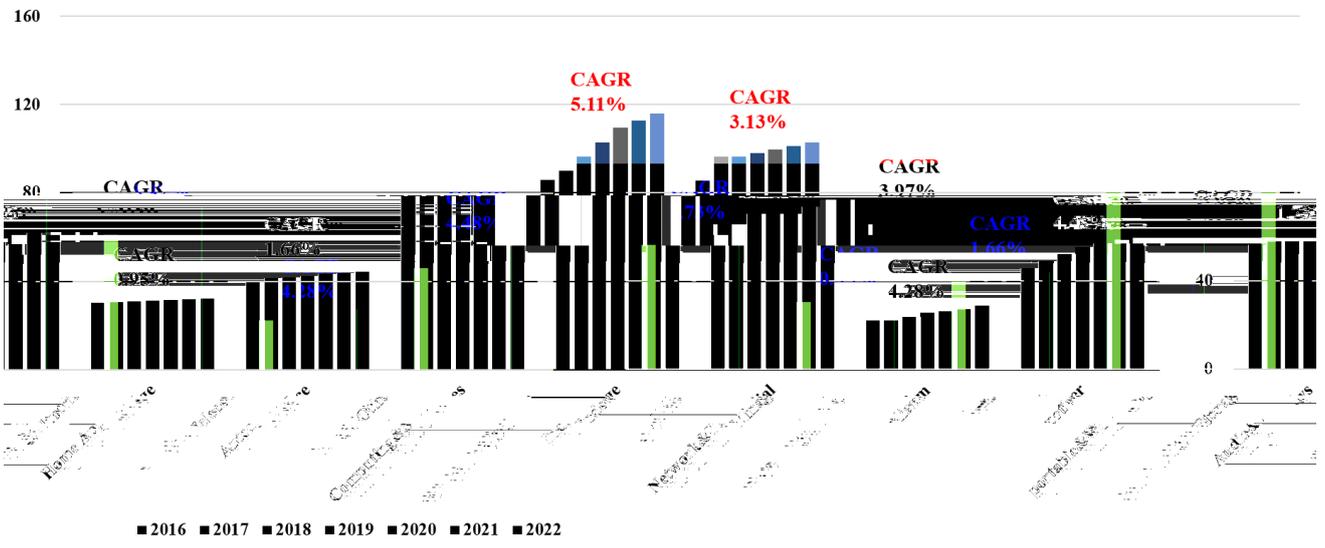
单位:万元	2019H1	2019	2018H1	2018H1	同比(2019H1-2018H1)	环比(2019H1-2018H1)
制造与服务	148672.05	1318552.04	1169629.99	1167676.52	1278%	1118%
晶圆制造	105984.39	234508.70	128524.31	109532.49	3.35%	1128%
封装测试	13.34%	36930.19	73262.09	36331.90	41178.30	11.50%
晶圆制造+封装测试	123.69%	271.06%	157.12%	145.95%	192.58%	168.55%
产品与方案	20.11%	-0.45%	114006.51	251566.21	137559.70	136938.18
功率半导体	11.01%	1.00%	102703.22	226011.40	123117.67	135737.01
其他	9.10%	0.55%	6172.78	6652.60	5019.72	1672.17
其他业务	3036.32	1698.97	2834%	-44.05%	1323.84	4360.11
合计	156900.40	574298.41	1310269.01	1308308.57	16.03%	1028%

Wind

1200V 650V SiC
6 SiC

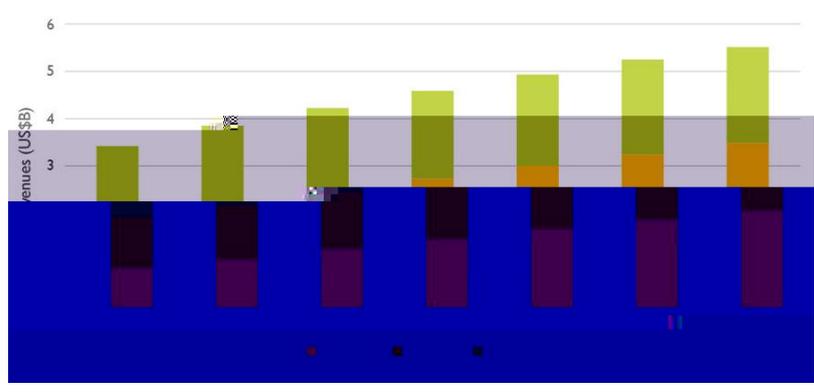
2 MOSFET

2016-2022功率MOSFET细分应用市场规模预测（亿元）



Yole

3 IGBT



Yole

2018 1 2016 4 2016 2017

“ ”

AA ABS R3 A B

“ ”

	6	15%	
	6	5%	15%
	6	-5%	5%
	6	5%	15%
	6	15%	
	6		
	6		
	6		

<http://www.nesc.cn> 400-600-0686

6666			130119
28	D		100033
729			200127
1006	34D		518038
	122	15	510630

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